

# Detectors for lonised (-ing) Particles





## Outline

- Introduction
- Radioactivity
- Particle interaction with matter
- Ionised particle detectors
- Assignments- Simulation Task



## Introduction

Detection of particles (or gamma photon, se also the presentations about photodetectors) from a radioactive decay means, the particles must interact with (ionising) the detector. The three necessary processes are:

- 1) Carrier generation by incident particle
- 2) Carrier transport (with or without carrier multiplication)
- 3) Interaction of current with external circuit to provide the output signal



## Radioactivity

- Spontaneous disintegration of atomic nuclei.
  - Alfa decay (He nucleus)
  - Beta decay (electron, positron)
  - Gamma decay (photon)



## Stopping Mechanism

• The total stopping power

 $S_{total} = S_n + S_e$ 

- $S_n$ : nuclear stopping,  $S_e$ : electronic stopping
- Low *E*, high *A* ion implantation: mainly nuclear stopping
- High *E*, low *A* ion implantation, electronic stopping mechanism is more important



Stopping Power and Ion Velocity



Ion Velocity





Simulation of stopping power can be done with SRIM software "SRIM.org"



- Ionisation of semiconductor
  - Particle and high energy photons (x-ray,gamma) result in an generation of one e/h-pair /~3Eg
  - For silicon is needed 3.6eV to generate one e/h-pair















n-Si Wafer

Oxide passivation

Opening of windows

Doping by ion implantation B 15 keV 5x10<sup>14</sup> cm<sup>-2</sup> As 30 keV 5x10<sup>15</sup> cm<sup>-2</sup>

Annealing at 600°C, 30 min

Al metallisation

Al pattering at the front Al-rear contact

- Passivated, silicon planar diode detector
- Almost operated with reverse bias voltage, (except photodiodes normally operated with zero bias voltage)

• J. Kemmer, Nucl. Instr. and Meth. 226, 45, (1984)





 Drift of generated carrier in the detector

 $v = \mu \cdot \overline{E}$  for v < vs

- Fast current pulse-high electric field in the detector
- High mobility for holes and electrons
- The mobility for holes are in most cases lower than electrons.





High reverse bias in the detector generate high electric field
Reverse bias 20 V





•Qf= $2 \cdot 10^{12} \, q/cm^2$ 

- •Vr=20V
- •Result in high electric field at anode





## And surface avalanche breakdown





•Edge termination

–Edge implantation(edge of anode) ordiffusion drive in





#### Edge termination –Field plate





#### •Edge termination –Floating guard rings, reverse bias 40 V, Qf=2.10<sup>12</sup> q/cm<sup>2</sup>





## **Assignments- Simulation Task**

- Simulate stopping power for 5 MeV  $\alpha-$  particle in silicon using SRIM
- Use the simulated data to generate an realistic e/h-pair generation in Medici
- As an Input file to medici use an file from tsupreme4 with the data;
  - 50x500um,
  - field oxide thickness=5000Å,
  - resitivity of bulk=20000 Ωcm, n-type Phos.,
  - detector window doping=950C, boron, 30 min  $N_2$  followed by 30 min  $O_2$
  - detector window opening width=30um



## **Assignments- Simulation Task**

- In medici use  $Qf=1.10^{11} q/cm^2$
- Simulate the current response with Vr=0V, Vr=100V and with generation of e/h pair (alfa particle) at front and at back of the detector, i.e. four different cases!
- Integrate the current pulse and compare the resulting charge collection for the four cases

